Six Pair, N- and P-Channel Enhancement-Mode MOSFET

Features

- Six N- and P-channel MOSFET pairs
- Integrated gate-to-source resistor
- Integrated gate-to-source Zener diode
- Low threshold
- Low on-resistance
- Low input capacitance
- Fast switching speeds
- Free from secondary breakdown
- Low input and output leakage

Applications

- High voltage pulsers
- Amplifiers
- Buffers
- Piezoelectric transducer drivers
- General purpose line drivers
- Logic level interfaces

General Description

The Supertex TC7320 consists of a six pairs of high voltage, low threshold, N- and P-channel MOSFETs in a 32-lead LQFP package. All of the MOSFETs have integrated gate-to-source resistors and gate-to-source Zener diode clamps which are desired for high voltage pulser applications. This low threshold, enhancement-mode (normally-off), transistor utilizes an advanced lateral DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Supertex's lateral DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	32-Lead LQFP *7.00x7.00mm body 1.60mm height (max) 0.80mm pitch*	BV_{DSS}/BV_{DGS} (V)		$R_{DS(ON)}$ (max) (Ω)	
		N-Channel	P-Channel	N-Channel	P-Channel
TC7320	TC7320FG-G	200	-200	20	20

-G indicates package is RoHS compliant ('Green')

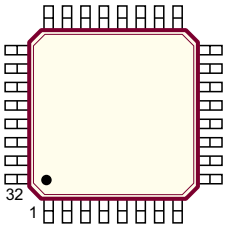
Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV_{DSS}
Drain-to-gate voltage	BV_{DGS}
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	+300°C
Power dissipation	1.5W

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

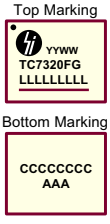
* *Distance of 1.6mm from case for 10 seconds.*

Pin Configuration



32-Lead LQFP (FG)

Package Marking



YY = Year Sealed
WW = Week Sealed
L = Lot Number
C = Country of Origin*
A = Assembler ID*
_____ = "Green" Packaging

**May be part of top marking*

Package may or may not include the following marks: Si or

32-Lead LQFP (FG)

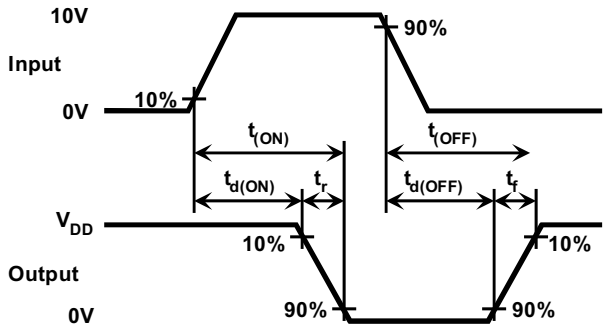
N-Channel Electrical Characteristics *(T_A = 25°C unless otherwise specified)*

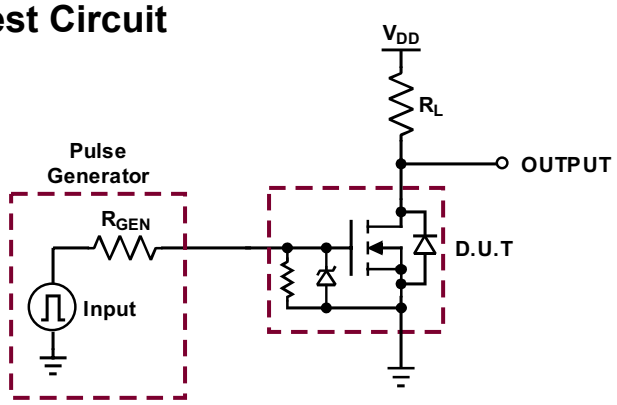
Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	200	-	-	V	V_{GS} = 0V, I_D = 1.0mA
$V_{GS(th)}$	Gate threshold voltage	-	0.4	-	V	V_{GS} = V_{DS}, I_D = 1.0mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	-4.5	mV/°C	V_{GS} = V_{DS}, I_D = 1.0mA
R_{GS}	Gate-to-source shunt resistor	0.8	-	2.0	KΩ	I_{GS} = 100µA
ΔR_{GS}	Change in R_{GS} with temperature	-	-7.5	-	%/°C	I_{GS} = 100µA
VZ_{GS}	Gate-to-source Zener voltage	10	-	18	V	I_{GS} = 2.0mA
ΔVZ_{GS}	Change in VZ_{GS} with temperature	-	-0.5	-	mV/°C	I_{GS} = 2.0mA
I_{DSS}	Zero gate voltage drain current	-	-	10.0	µA	V_{DS} = Max rating, V_{GS} = 0V
		-	-	1.0	mA	V_{DS} = 0.8 Max Rating, V_{GS} = 0V, T_A = 125°C
$I_{D(ON)}$	On-state drain current	1.0	-	-	A	V_{GS} = 10V, V_{DS} = 25V
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	-	20	Ω	V_{GS} = 10V, I_D = 150mA
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	0.6	1.0	%/°C	V_{GS} = 10V, I_D =150mA
G_{FS}	Forward transconductance	-	150	-	mmho	V_{DS} = 25V, I_D = 200mA
C_{ISS}	Input capacitance	-	-	150	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz
C_{OSS}	Common source output capacitance	-	-	75		
C_{RSS}	Reverse transfer capacitance	-	-	25		
$t_{d(ON)}$	Turn-on delay time	-	-	12	ns	V_{DD} =25V, I_D = 500mA, R_{GEN} = 25Ω
t_r	Rise time	-	-	15		
$t_{d(OFF)}$	Turn-off delay time	-	-	25		
t_f	Fall time	-	-	40		
V_{SD}	Diode forward voltage drop	-	-	1.8	V	V_{GS} = 0V, I_{SD} = 500mA
t_{rr}	Reverse recovery time	-	300	-	ns	V_{GS} = 0V, I_{SD} = 500mA

Notes:

1. *All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)*
2. *All A.C. parameters sample tested.*

N-Channel Switching Waveforms and Test Circuit





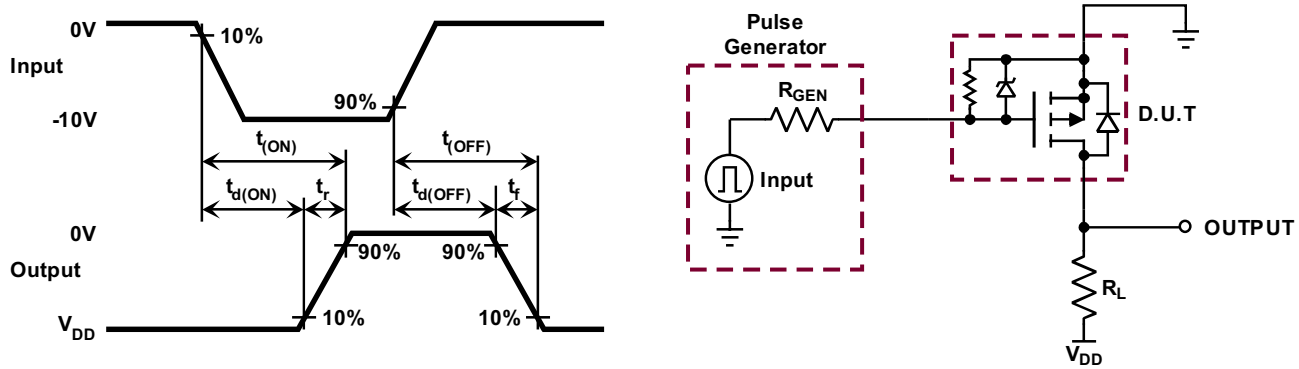
P-Channel Electrical Characteristics (T_A = 25°C unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	-200	-	-	V	V_{GS} = 0V, I_D = -1.0mA
$V_{GS(th)}$	Gate threshold voltage	-	-2.3	-	V	V_{GS} = V_{DS}, I_D = -1.0mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	4.5	mV/°C	V_{GS} = V_{DS}, I_D = -1.0mA
R_{GS}	Gate-to-source shunt resistor	0.8	-	2.0	KΩ	I_{GS} = -100µA
ΔR_{GS}	Change in R_{GS} with temperature	-	-7.5	-	%/°C	I_{GS} = -100µA
VZ_{GS}	Gate-to-source Zener voltage	10	-	18	V	I_{GS} = -2.0mA
ΔZ_{GS}	Change in VZ_{GS} with temperature	-	-0.5	-	mV/°C	I_{GS} = -2.0mA
I_{DSS}	Zero gate voltage drain current	-	-	-10	µA	V_{DS} = Max rating, V_{GS} = 0V
		-	-	-1.0	mA	V_{DS} = 0.8 Max Rating, V_{GS} = 0V, T_A = 125°C
$I_{D(ON)}$	On-state drain current	-1.0	-	-	A	V_{GS} = -10V, V_{DS} = -25V
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	-	20	Ω	V_{GS} = -10V, I_D = -150mA
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	0.6	1.0	%/°C	V_{GS} = -10V, I_D =-150mA
G_{FS}	Forward transconductance	-	150	-	mmho	V_{DS} = -25V, I_D = -200mA
C_{ISS}	Input capacitance	-	-	200	pF	V_{GS} = 0V, V_{DS} = -25V, f = 1.0MHz
C_{OSS}	Common source output capacitance	-	-	100		
C_{RSS}	Reverse transfer capacitance	-	-	35		
$t_{d(ON)}$	Turn-on delay time	-	-	15	ns	V_{DD} = -25V, I_D = -500mA, R_{GEN} = 25Ω
t_r	Rise time	-	-	20		
$t_{d(OFF)}$	Turn-off delay time	-	-	35		
t_f	Fall time	-	-	30		
V_{SD}	Diode forward voltage drop	-	-	-1.8	V	V_{GS} = 0V, I_{SD} = -500A
t_{rr}	Reverse recovery time	-	300	-	ns	V_{GS} = 0V, I_{SD} = -500A

Notes:

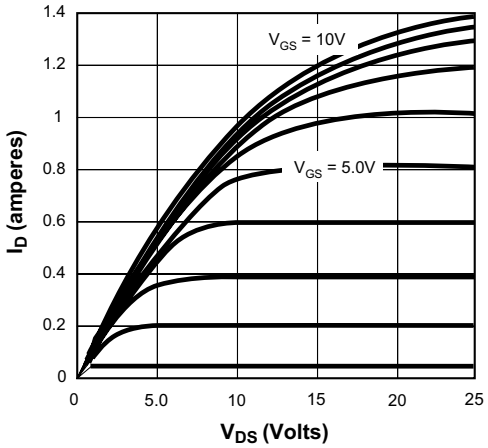
1. *All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)*
2. *All A.C. parameters sample tested.*

P-Channel Switching Waveforms and Test Circuit

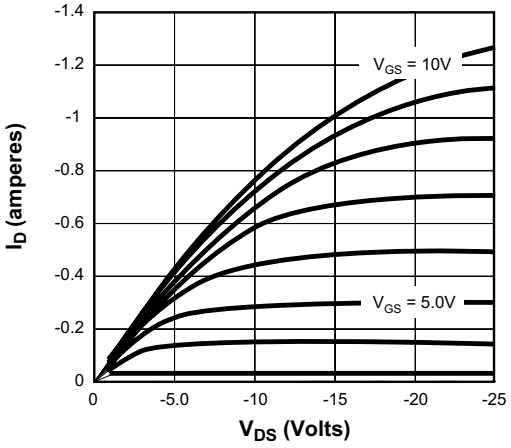


Typical I-V Characteristics

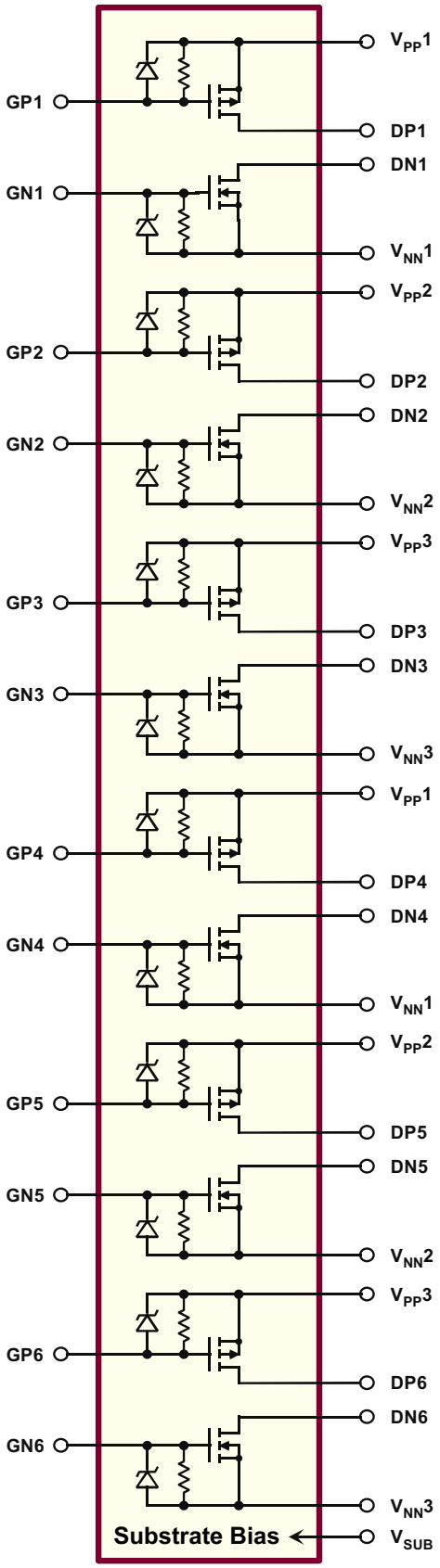
N-Channel



P-Channel



Block Diagram



Pin Descriptions

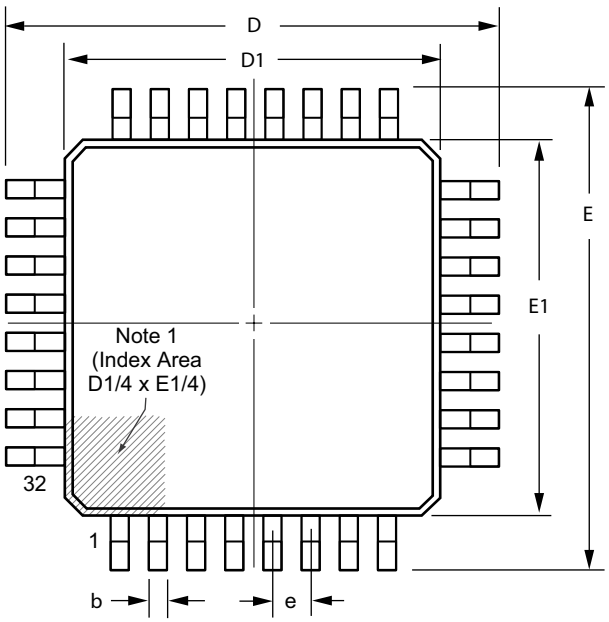
Pin #	Function
1	GP1
2	GN1
3	GN2
4	GN3
5	GN6
6	GN5
7	GN4
8	GP4
9	GP5
10	GP6
11	DP6
12	$V_{PP}2$
13	DP5
14	DP4
15	V_{SUB}*
16	$V_{NN}3$

Pin #	Function
17	DN6
18	DN3
19	DN5
20	N/C
21	$V_{NN}2$
22	DN2
23	DN4
24	DN1
25	$V_{NN}1$
26	$V_{PP}1$
27	DP1
28	DP2
29	$V_{PP}3$
30	DP3
31	GP3
32	GP2

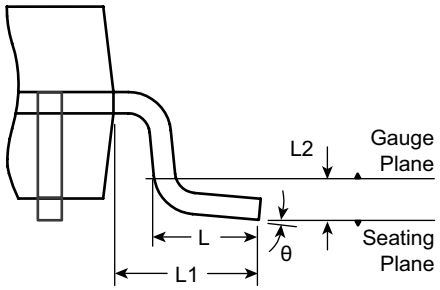
** The V_{SUB} pin needs to be connected to the most positive supply*

32-Lead LQFP Package Outline (FG)

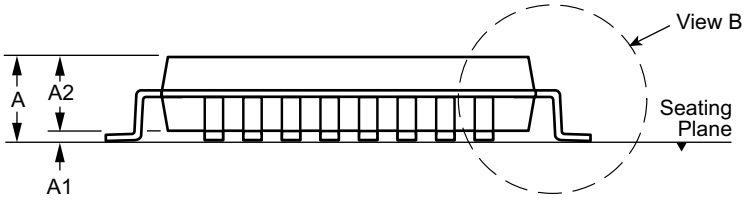
7.00x7.00mm body, 1.60mm height (max), 0.80mm pitch



Top View



View B



Side View

Note:

1. *A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.*

Symbol		A	A1	A2	b	D	D1	E	E1	e	L	L1	L2	θ
Dimension (mm)	MIN	1.40*	0.05	1.35	0.30	8.80*	6.80*	8.80*	6.80*	0.80 BSC	0.45	1.00 REF	0.25 BSC	0°
	NOM	-	-	1.40	0.37	9.00	7.00	9.00	7.00		0.60			3.5°
	MAX	1.60	0.15	1.45	0.45	9.20*	7.20*	9.20*	7.20*		0.75			7°

JEDEC Registration MS-026, Variation BBA, Issue D, Jan. 2001.

** This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.*

Drawings are not to scale.

***Supertex Doc. #:** DSPD-32LQFPFG, Version E101708.*

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

Supertex inc.
1235 Bordeaux Drive, Sunnyvale, CA 94089
Tel: 408-222-8888
www.supertex.com